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Mar 6, 2001

PUB-NO: JP02001059191A

DOCUMENT-IDENTIFIER: JP 2001059191 A

TITLE: ETCHING AGENT, PRODUCTION OF SUBSTRATE FOR ELECTRONIC EQUIPMENT USING THE SAME AND ELECTRONIC EQUIPMENT

PUBN-DATE: March 6, 2001

INVENTOR-INFORMATION:

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APPL-NO: JP20000001127

APPL-DATE: January 6, 2000

INT-CL (IPC): C23F 1/18; C09K 13/00; C09K 13/06; H01L 21/308; H01L 21/3205; H01L 29/786; H01L 21/336

ABSTRACT:

PROBLEM TO BE SOLVED: To provide an etching agent capable of etching a Cu film by an easy chemical etching method being a dipping method by rest process in the case that a Cu film of low resistance is used as a wiring material, small in the secular change of the etching grade and capable of preventing the occurrence of a pattern thinning phenomenon caused by the dispersion of the side etching amount of the Cu film.

SOLUTION: This etching agent consists of an aq. soln. contg. potassium peroxymonosulfate monohydrogen and hydrofluoric acid. In this method for producing a thin film transistor substrate, on the surface of a laminated film obtd. by successively laminating a Ti film or a Ti alloy 3 and a Cu film 4 on a substrate 2, masks 27 and 28 of prescribed patterns are formed, the laminated film is subjected to etching by using the etching agent having the compsn., and a gate electrode 5 (laminated wiring) 5 and a lower pad layer (laminated wiring) 16b of the prescribed patterns are formed.

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19 and (peroxosulfate)

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| USPT,PGPB,JPAB,EPAB,DWPI,TDBD | I6 same (acetic acid) | 949 | <u>L9</u> |
| USPT,PGPB,JPAB,EPAB,DWPI,TDBD | I6 same (potassium near hydrogen near peroxomonosulfate or "KH S.sub.5" or "NaH S.sub.5") | 0 | <u>L8</u> |
| USPT,PGPB,JPAB,EPAB,DWPI,TDBD | I6 same (peroxomonosulfate) | 1 | <u>L7</u> |
| USPT,PGPB,JPAB,EPAB,DWPI,TDBD | copper same (etch\$3 or remov\$3 or polish\$3) | 70589 | <u>L6</u> |
| JPAB | 11-173431 | 0 | <u>L5</u> |
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| JPAB | 2001059191 | 1 | <u>L3</u> |
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| USPT,JPAB | 173431 | 16 | <u>L1</u> |

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